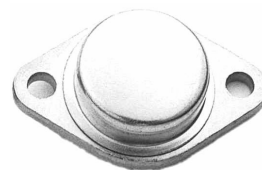


2N3773

Silicon NPN Transistors

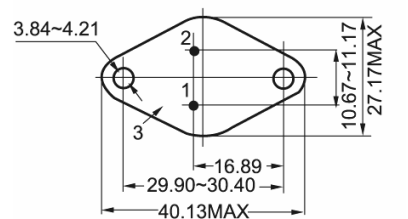
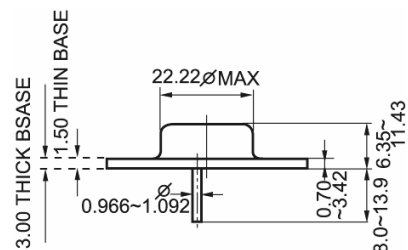


◆ Features

- Used in power switching circuits such as relay or solenoid drivers
- With TO-3 package

◆ Absolute Maximum Ratings $T_c=25^{\circ}\text{C}$

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	160	V
V_{CEO}	Collector to emitter voltage	140	V
V_{EBO}	Emitter to base voltage	7.0	V
I_{CP}	Peak collector current	30	A
I_C	Collector current	16	A
P_C	Collector power dissipation	150	W
T_j	Junction temperature	-65~200	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-65~200	$^{\circ}\text{C}$



TO-3

◆ Electrical Characteristics $T_c=25^{\circ}\text{C}$

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{CBO}	Collector-base cut-off current	$V_{CB}=140\text{V}, I_E=0$		2.0	mA
I_{EBO}	Emitter-base cut-off current	$V_{BE}=7\text{V}, I_C=0$		5.0	mA
I_{CEO}	Collector-emitter cut-off current	$V_{CE}=120\text{V}, I_B=0$		10	mA
V_{CBO}	Collector-base breakdown voltage				
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=200\text{mA}, I_B=0$	140		V
V_{EBO}	Emitter-base breakdown voltage				
$V_{CEsat-1}$	Collector-emitter saturation voltages	$I_C=8\text{A}, I_B=800\text{mA}$		1.4	V
$V_{CEsat-2}$	Collector-emitter saturation voltages	$I_C=16\text{A}, I_B=3.2\text{A}$		4.0	V
$V_{CEsat-3}$	Collector-emitter saturation voltages				
$V_{CEsat-4}$	Collector-emitter saturation voltages				
h_{FE-1}	Forward current transfer ratio	$I_C=8\text{A}, V_{CE}=4\text{V}$	15	60	
h_{FE-2}	Forward current transfer ratio	$I_C=16\text{A}, V_{CE}=4\text{V}$	5.0		
h_{FE-3}	Forward current transfer ratio				
h_{FE-4}	Forward current transfer ratio				
$V_{BE(sat)1}$	Base-emitter saturation voltages	$I_C=8\text{A}, V_{CE}=4\text{V}$		2.2	V
$V_{BE(sat)2}$	Base-emitter saturation voltages				
$V_{BE(sat)3}$	Base-emitter saturation voltages				
f_T	Transition frequency at $f=1\text{MHz}$				
t_f	Fall time				
t_s	Turn-off storage time				